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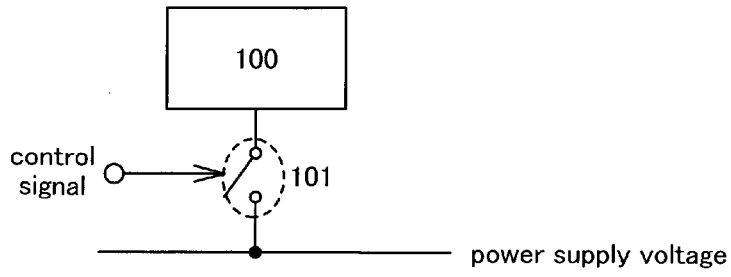
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(54) Title: SEMICONDUCTOR DEVICE

FIG. 1



(57) Abstract: An object is to provide a semiconductor device with reduced standby power. A transistor including an oxide semiconductor as an active layer is used as a switching element, and supply of a power supply voltage to a circuit in an integrated circuit is controlled by the switching element. Specifically, when the circuit is in an operation state, supply of the power supply voltage to the circuit is performed by the switching element, and when the circuit is in a stop state, supply of the power supply voltage to the circuit is stopped by the switching element. In addition, the circuit supplied with the power supply voltage includes a semiconductor element which is a minimum unit included in an integrated circuit formed using a semiconductor. Further, the semiconductor included in the semiconductor element contains silicon having crystallinity (crystalline silicon).

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